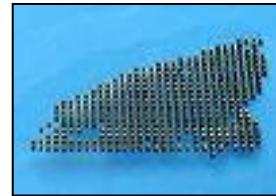




APD200-CHIP

- InGaAs Avalanche Photodiode
- Ø 0.2 mm active area
- 0.95 – 1.65 µm spectral range
- Low Leakage Current and Noise
- ≥700 MHz 3 dB Bandwidth
- Low Stray Absorption



Description

APD200-CHIP is an **InGaAs avalanche photodiode chip die** with an active area diameter of **0.2 mm**, offering a very low leakage current and noise, a spectral sensitivity range from **0.95 to 1.65 µm** and low stray absorption.

It is widely used for spectral analysis, optical coherence tomography, SWIR camera, light detection, and LIDAR applications.

Maximum Ratings ($T_{CASE}=25^\circ\text{C}$)

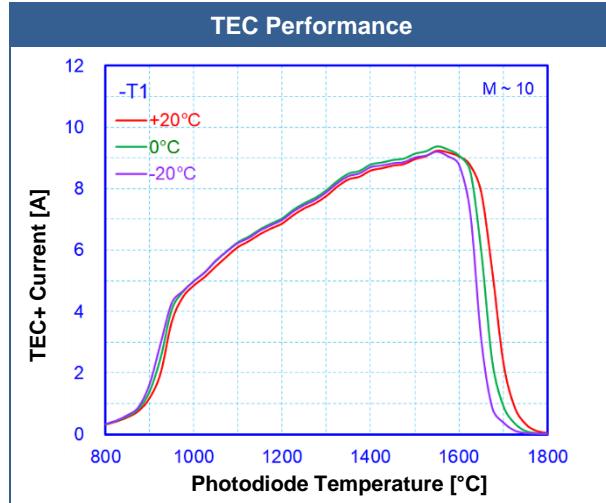
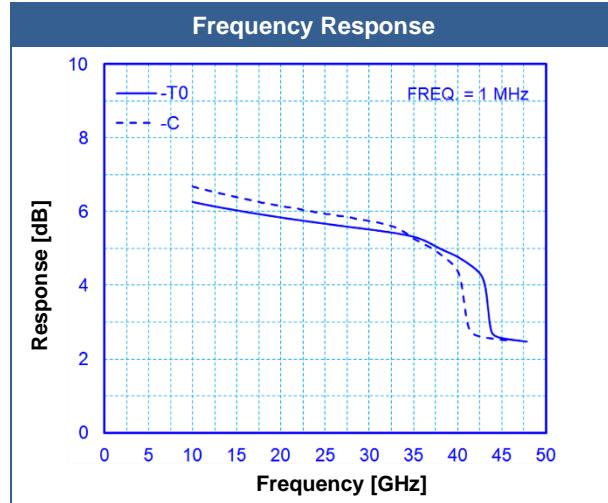
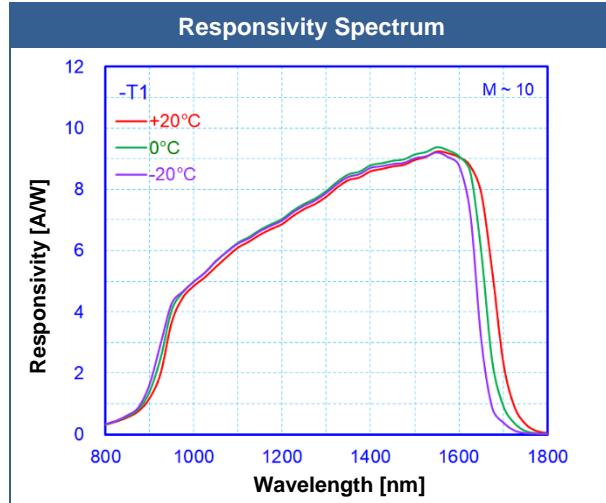
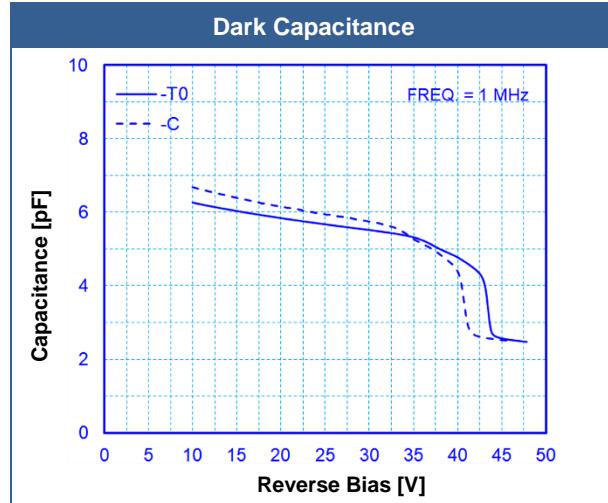
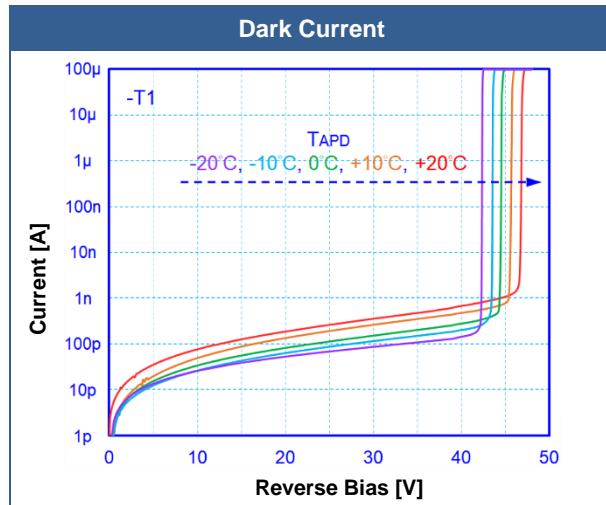
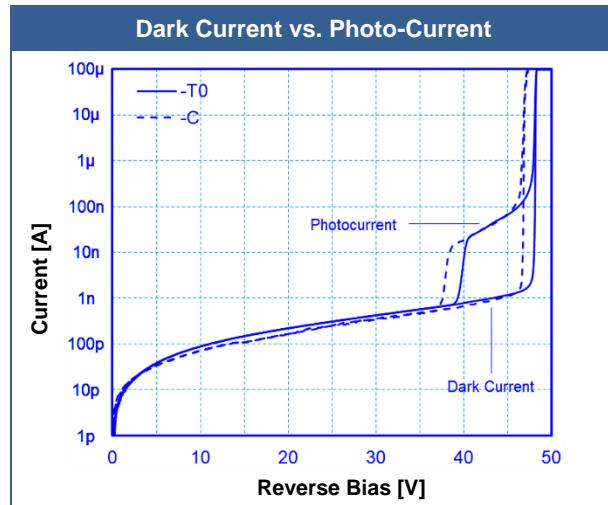
Parameter	Symbol	Min.	Values	Max.	Unit
Reverse Current	I_R			1	mA
Forward Current	I_F			5	mA
Operating Temperature	T_{CASE}	- 40		+ 85	°C
Storage Temperature	T_{STG}	- 55		+ 125	°C

Electro-Optical Characteristics ($T_{CASE}=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min.	Values	Typ.	Max.	Unit
Spectral Range	λ		0.95		1,65		µm
Aperture Diameter	Ø			200			µm
Peak Sensitivity	λ_P	$V_R=0\text{V}$					µm
Dark Current	I_D	$M=10$		5	50	nA	
Operating Voltage	V_{OP}	$M=10$	32		50		V
Breakdown Voltage	V_{BD}	$I_{BD}=100\mu\text{A}$	35		55		V
Capacitance	C_J	$M=10, f=1\text{MHz}$		2.5	3.0		
Responsivity	S_λ	$M=10, \lambda=1.55\mu\text{m}$	8	9			A/W
Useable Gain	T	$\lambda=1.55\mu\text{m}$	10	20			
3dB Bandwidth		$M=10, \lambda=1.55\mu\text{m}, 50\Omega$	0.7	0.85			GHz
Spectral Noise Current		$M=10, \Delta\lambda=1\text{kHz}$		0.5	1.5		pA/ $\sqrt{\text{Hz}}$
Temperature Coefficient of V_{BD}				0.10	0.15		V/ $^\circ\text{C}$

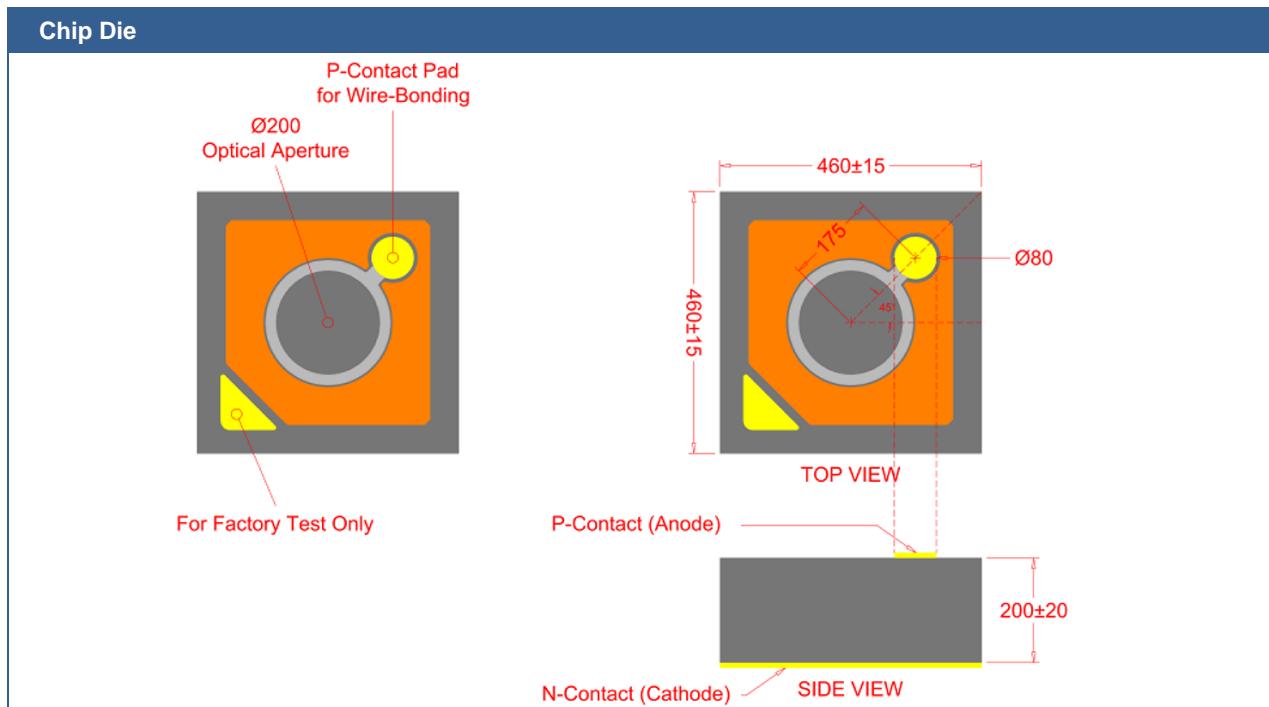


Typical Performance Curves





Outline Dimensions



All Dimensions in mm

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The above specifications are for reference purpose only and subjected to change without prior notice